



AF ITW

98 P 1379 D

BOX AF

CERTIFICATION OF MAILING OR FAX TRANSMISSION

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 or facsimile transmitted to the U.S. Patent and Trademark Office on the date shown below.

By: Longfeng Chen

Date: December 9, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 09/885,553 Confirmation No. 6319  
Applicant : Lars-Peter Heineck et al.  
Filed : June 20, 2001  
TC/A.U. : 2826  
Examiner : Johannes P. Mondt  
Title: : MOS Transistor in a Single-Transistor Memory  
Cell Having a Locally Thickened Gate Oxide  
  
Docket No. : GR 98 P 1379 D  
Customer No. : 24131

BOX AF

Hon. Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AMENDMENT under 37 C.F.R. § 1.116**

S i r :

In response to the final Office action dated September 17, 2004, please amend the above-identified application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 4 of this paper.